

Silicon NPN Power Transistors

2SD1497

DESCRIPTION

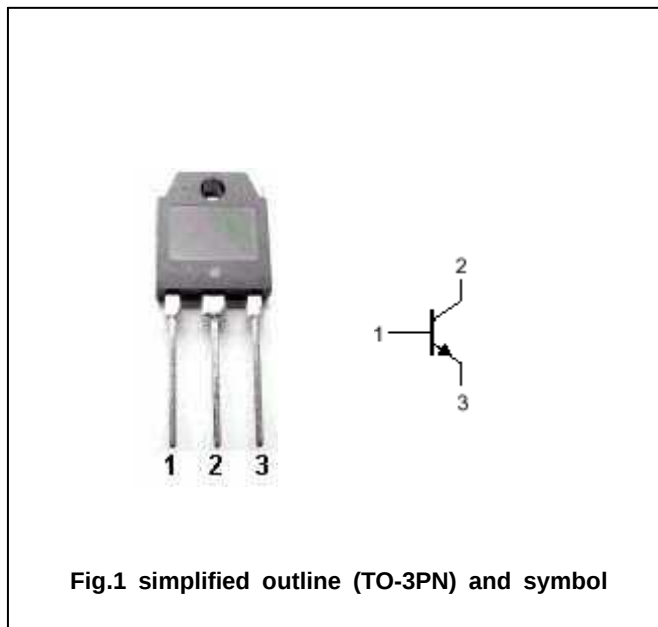
- With TO-3PN package
- High voltage ,high reliability
- Wide area of safe operation

APPLICATIONS

- High voltage power switching TV horizontal deflection output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings (Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1500	V
V_{CEO}	Collector-emitter voltage	Open base	600	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current		6	A
I_{CM}	Collector current-peak		7	A
$I_{C(surge)}$	Collector surge current		16	A
P_C	Collector power dissipation	$T_C=25^{\circ}\text{C}$	50	W
T_j	Junction temperature		150	$^{\circ}\text{C}$
T_{stg}	Storage temperature		-45~150	$^{\circ}\text{C}$

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=10mA$; $I_C=0$	7			V
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=10mA$; $R_{BE}=\infty$	600			V
V_{CESat}	Collector-emitter saturation voltage	$I_C=5A$; $I_B=1A$			5.0	V
V_{BESat}	Base-emitter saturation voltage	$I_C=5A$; $I_B=1A$			1.5	V
I_{CEX}	Collector cut-off current	$V_{CE}=1500V$; $V_{BE}=1.5V$			1.0	mA
I_{EBO}	Emitter cut-off current	$V_{EB}=7V$; $I_C=0$			1.0	mA
h_{FE-1}	DC current gain	$I_C=0.3A$; $V_{CE}=5V$	10		30	
h_{FE-2}	DC current gain	$I_C=5A$; $V_{CE}=5V$	5			
t_f	Fall time	$I_{CP}=4A$; $I_{B1}=1.3A$; $L_B=0$			2.0	μs

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